New Jersey Semi-Conductor Products, Inc.

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PN4117A

N-Channel Switch

 This device is designed for low current DC and audio application. These devices provide excellent performance as input stages for subpicoamp instrumentation or any high impedance signal sources.

Sourced from process 53.



TO-92 1. Drain 2. Source 3. Gate

Absolute Maximum Ratings * T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{DG}	Drain-Gate Voltage	40	V	
V _{GS}	Gate-Source Voltage	-40	V	
GF	Forward Gate Current	50	mA	
Т _{stg}	Operating and storage Temperature Range	- 55 ~ 150		

serviceability of any semiconductor device may be impaired

NOTES:

These ratings are based on a maximum junction temperature of 150degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Electrical Characteristics TA=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Chara	cteristics					
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$V_{DS} = 0, I_G = -1\mu A$	-40]	v –
V _{GS} (off)	Gate-Source Cutoff Voltage	V _{DS} = -10V, I _D = 1.0nA	-0.6	-	-1.8	v -
IGSS	Gate Reverse Current	$V_{DS} = 0V, V_{GS} = -20V$	-		-1.0	pA
On Chara	cteristics					
IDSS	Zero-Gate Voltage Drain Current *	V _{DS} = 10V, V _{GS} = 0	30		90	μA
Small Sig	nal Characteristics			L		
gfs	Common Source Forward Transconductance	V _{DS} = 10V, V _{GS} = 0 f = 1.0KHz	70		210	mmhos
g _{oss}	Common Source Output Conductance	V_{DS} = 10V, V_{GS} = 0 f = 1KHz			3.0	mmhos
R _{E(YFS)}	Common Source Forward Conductance	$V_{DS} = 10V, V_{GS} = 0$ f = 30MHz	60			mmhos
C _{ISS}	Input Capacitance	V _{DS} = 10V, V _{GS} = 0 f = 1.0KHz			3.0	pF
C _{rss}	Reverse Transfer Capacitance	$V_{DS} = 10V, V_{GS} = 0$ f = 1.0MHz			1.5	рF

* Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 1.0%

Thermal Characteristics TA=25°C unless otherwise noted

Symbol	Parameter	Max.	Units	
PD	Total Device Dissipation	350	mW	
	Derate above 25°C	2.8	mW/°C	
R _{θJC}	Thermal Resistance, Junction to Case	125	°C/W	
R _{0JA}	Thermal Resistance, Junction to Ambient	357	°C/W	



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977



TO-92 (92,94,96)

Z	ç	2	94		96	
ā	В	F	В	F	В	F
1	E	D	Е	D	В	S
2	В	S	С	G	Ε	D
3	С	G	В	S	С	G